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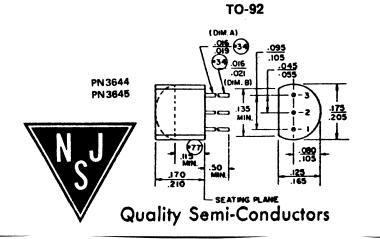
2N3644 · 2N3645 · PN3644 · PN3645

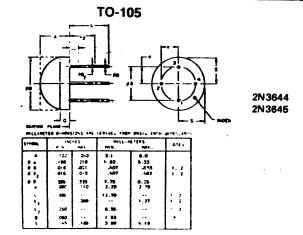
PNP SMALL SIGNAL GENERAL PURPOSE AMPLIFIERS AND SWITCHES

ABSOLUTE M	AXIMUM RATINGS		,		
Maximum 1	l'emperatures	2N3644/45	PN3644/45		
Storage Temperature		-55°C to +125°C	-55°C to +150°C		
Operation	ng Junction Temperature	125°C	150°C		
Lead Te	mperature (10 seconds)	260°C	260° C		
	ower Dissipation (Notes 2 & 3)				
Total Dissipation at 25°C Case Temperature		0.07 W	1.0 W		
	at 25°C Ambient Temperature	0.3 W	0.625 W		
Maximum \	oltages and Current	2N/PN3645	2N/PN3644		
V _{СВО}	Collector to Base Voltage	-60 V	-4 5 ∨		
VCEO	Collector to Emitter Voltage (Note 4)	-60 ∨	-45 V		
VEBO	Emitter to Base Voltage	-5.0 V	-5.0 V		
lc	Collector Current	500 mA	500 mA		

ELECTRICAL CHARACTERISTICS (25°C Ambient Temperature unless otherwise noted)

SYMBOL	CHARACTERISTIC		3644 3644 MAX.		3645 3645 MAX.	UNITS	TEST CONDITIONS
hFE	DC Current Gain	40		40			I _C = 100 μA, V _{CE} = -10 V
		80		80			I _C = 1.0 mA, V _{CE} = -10 V
pEE .	DC Pulse Current Gain	100		100			I _C = 10 mA, V _{CE} = -10 V
		80	240	80	240		I _C = 50 mA, V _{CE} = 1.0 V
		100	300	100	300		I _C = 150 mA, V _{CE} = -10 V
•	ļ·	20		20			I _C = 300 mA, V _{CE} = -2.0 V
h _{fe}	High Frequency Current Gain	2.0		2.0			$I_C = 20 \text{ mA}, V_{CE} = -20 \text{ V}, f = 100 \text{ MHz}$
Cop	Output Capacitance		8.0		8.0	pF	IE = 0, V _{CB} = -10 V, f = 140 kHz
C _{ib}	Input Capacitance		35		35	pF	I _C = 0, V _{EB} = -0.5 V, f = 140 kHz
VCE(sat)	Pulsed Collector		-0.25		-0.25	٧	Ic = 50 mA, IB = 2.5 mA
	Saturation Voltage		-0.4		-0.4	V	IC = 150 mA, IB = 15 mA
			-1.0		-1.0	V	IC = 300 mA, IB = 30 mA
VCEO(sus)	Collector to Emitter Sustaining Voltage	-45		-60		V	I _C = 10 mA (pulsed), I _B = 0
VBE(sat)	Pulsed Base		-1.0		-1.0	V	I _C = 50 mA, I _B = 2.5 mA
			-1.3		-1.3	V	IC = 150 mA, IB = 15 mA
		-0.8	-2.0	-0.8	-2.0	V	I _C = 300 mA, I _B = 30 mA
BVEBO	Emitter to Base Breakdown Voltage	-5.0			-5.0	V	IC = 0, IE = 10 μA
BVCBO	Collector to Base Breakdown Voltage	-45		-60		V	$I_{C} = 100 \mu\text{A}, I_{E} = 0$
ton	Turn On Time		40		40	ns	$I_C \approx 300 \text{mA}$, $I_{B1} \approx 30 \text{mA}$,
							V _{CC} = -30 V
toff	Turn Off Time		100		100	ns	$I_C \approx 300 \text{ mA}$, $I_{B1} \approx I_{B2} \approx 30 \text{ mA}$,
							V _{CE} = -30 V
CES	Collector Reverse Current		35			nA	V _{CE} = -30 V, V _{BE} = 0
					35	nA	V _{CE} = -50 V, V _{BE} = 0
			2.0			μΑ	V _{CE} = -30 V, V _{BE} = 0, T _A = 65°C
			1		2.0	μΑ	V _{CE} = -50 V, V _{BE} = 0, T _A = 65°C





2N3639 • 2N3640 • MPS3639 • MPS3640

ELECTRICAL CHARACTERISTICS (25°C Ambient Temperature unless otherwise noted) (Cont'd)

SYMBOL	CHARACTERISTIC	2N: MIN.	3639 MAX.	2N: MIN.	3640 MAX.	UNITS	TEST CONDITIONS
C _{ob}	Output Capacitance		3.5 5.5		3.5 5.5	pF pF	I _E = 0, V _{CB} = -5.0 V, f = 140 kHz I _E = 0, V _{CB} = 0, f = 140 kHz
Cib	Input Capacitance		3.5		3.5	pF	IC = 0, VEB = -0.5 V, f = 140 kHz
BVCBO	Collector to Base Breakdown Voltage	-6.0		, -12		v	IC = 100 μA, IE = 0
BVCES	Collector to Emitter Breakdown Voltage	-6.0		-12		V	I _C = 100 μA, V _{BE} = 0
VCEO(sus)	Collector to Emitter Sustaining Voltage (Note 4)	-6.0		-12		v	I _C = 10 mA, I _B = 0
BVEBO	Emitter to Base Breakdown Voltage	-4.0		-4.0		V	I _E = 100 μA, I _C = 0
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SYMBOL	CHARACTERISTIC	MIN.	3639 MAX.	MIN.	3640 MAX.	UNITS	TEST CONDITIONS
ton	Turn on Time	1				 	I _C ~ 50 mA, I _{R1} ~ 5.0 mA,
	(see test circuit no. 235)		25		25	ns	V _{CC} = 6.0 V
	(see test circuit no. 219)		60		60	ns	IC ≈ 10 mA, I _{B1} ≈ 0.5 mA,
			,		•	"	V _{CC} = -1.5 V
^t off	Turn Off Time	ı					IC ~ 50 mA, IB1 ~ IB2 ~ 5.0 mA,
	(see test circuit no. 235)		25		35	ns	V _C C = -6.0 V
	(see test circuit no. 219)		60		75	ns	IC ≈ 10 mA, IB1 ≈ IB2 ≈ 0.5 mA,
							Vcc = 1.5 V
h _{fe}	High Frequency Current Gain	3.0					IC = 10 mA, V _{CB} = 0, f = 100 MHz
		5.0		5.0			$I_{C} = 10 \text{ mA}, V_{CE} = -5.0 \text{ V},$
							f = 100 MU=
hFE	DC Pulse Current Gain (Note 4)	30	120	30	120		IC = 10 mA, V _{CE} = -0.3 V
		20		20	, 20		IC = 50 mA, V _{CE} = -1.0 V
V _{CE} (sat)	Collector to Emitter Saturation		-0.16		-0.2	V	IC = 10 mA, IB = 1.0 mA,
	Voltage (Note 4)		-0.5		-0.6		Ic = 50 mA, IB = 5.9 mA
			-0.23		-0.25	V	IC = 10 mA, IB = 1.0 mA,
							T _A = 65°C
V _{BE} (sat)	Base Saturation Voltage	-0.75	-0.95	-0.75	-0.95	V	IC = 10 mA, IB = 0.5 mA
	(Note 4)	-0.8	-1.0	-0.8	-1.0	V	IC = 10 mA, IB = 1.0 mA
			1.5		1.5	V	IC = 50 mA, IR = 5.0 mA
CES	Collector Reverse Current		10			nA	V _{CE} = -3.0 V, V _{BE} = 0
					10	nA	V _{CE} = -6.0 V, V _{BE} = 0
			1.0			μΑ	$V_{CE} = -3.0 \text{ V}, V_{BE} = 0,$
					i		T _A = 65°C
					1.0	μА	V _{CE} = -6.0 V, V _{BE} = 0,
					1		T _A = 65°C
Cob	Output Capacitance		3.5		3.5	pF	$I_{E} = 0$, $V_{CB} = -5.0 \text{ V}$,
			l		1		f = 140 kHz
C _{ib}	Input Capacitance		3.5		3.5	pF	$I_{C} = 0, V_{EB} = -0.5 V$
					İ		f = 140 kHz
BVCBO	Collector to Base Breakdown	-6.0		-12		v	IC = 100 μA, IE = 0
B\/	Voltage						
BVCES	Collector to Emitter Breakdown Voltage	-6.0	1	-12	1	V.	IC = 100 μA, V _{BE} - 0
VCEO(sus)	Collector to Emitter Sustaining	0.0		4.5	1		e e e e e e e e e e e e e e e e e e e
CEO(SUS)	Voltage (Note 4)	-6.0		-12		v	$I_C = 10 \text{ mA}, I_B = 0$
BVEBO	Emitter to Base Breakdown	-4.0		-4.0		v d	I _E = 100 μA, I _C = 0
	Voltage						<u>-</u>
			1				
						*,	